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AP20 Rec'd PCT/PTO 24 JAN 2006

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent Application of)
SUDA et al.)
Application Number: To Be Assigned)
Filed: Concurrently Herewith)
For: FIELD EFFECT TRANSISTOR AND METHOD FOR)
MANUFACTURING SAME)
ATTORNEY DOCKET NO. HIRA.0217)

Honorable Assistant Commissioner
for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified National Stage U.S. patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each foreign patent, or each publication or portion thereof listed or herein identified, is submitted herewith.

CERTIFICATION

This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

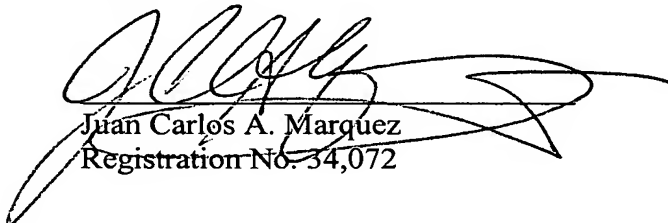
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Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER HIRA.0217	SERIAL NUMBER To be Assigned 10/565.624
	APPLICANT SUDA et al.	
	FILING DATE Concurrently Herewith	GROUP

U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	5,900,648	5/4/99	Harris et al.			3/28/97

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
						Yes	No
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	2001-094099	9/21/99	Japan			Abstract	X
	2002-246594	12/21/2001	Japan			Abstract	X
	FR 2 707 425	7/9/93	France			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

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EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

PTO1449